

 $R_{DS(ON)} = 3.2 m \Omega(Typ.) @V_{GS} = 10V$ 

Advanced HEFET® Technology

• Ultra Low On-Resistance

Excellent Q<sub>g</sub>xR<sub>DS(on)</sub> Product
100% avalanche tested

• 175°C Operating Temperature

· Lead Free and Green Devices Available (RoHS Compliant)

http://www.xpxbdt.com

XPX150N10TU

100V N-Channel Enhancement Mode Power MOSFET

## **Features** • 100V/150A,

## Applications

- Motor Drives
- Uninterruptible Power Supplies
- DC/DC converter
- General Purpose Applications

#### • Pin Configurations



## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit						
Common R	Common Ratings (T <sub>c</sub> =25°C Unless Otherwise Noted)								
V <sub>DSS</sub>	Drain-Source Voltage		100	V					
V <sub>GSS</sub>	Gate-Source Voltage		±25	v					
TJ	Maximum Junction Temperature		175	°C					
T <sub>STG</sub>	Storage Temperature Range		-55 to 175	°C					
ا <sub>s</sub>	Diode Continuous Forward Current	75	А						
Mounted or	Mounted on Large Heat Sink								
$I_{DP}^{(1)}$	300µs Pulse Drain Current Tested	T <sub>C</sub> =25°C	600	А					
. ②	$T_{c}=25^{\circ}C$		150	^					
$I_{D}^{(2)}$	Continuous Drain Current(V <sub>GS</sub> =10V)	106	A						
Р	Maximum Dawar Diasination	200	14/						
PD	$P_D$ Maximum Power Dissipation $T_C=100^{\circ}C$		100	W					
$R_{ ext{ heta}JC}$	Thermal Resistance-Junction to Case	0.75	°C/W						
$R_{ ext{ heta}JA}$	Thermal Resistance-Junction to Ambient	62.5	°C/W						
Drain-Source Avalanche Ratings									
E <sub>AS</sub> <sup>③</sup>	Avalanche Energy, Single Pulsed	440	mJ						



## 100V N-Channel Enhancement Mode Power MOSFET

## **Electrical Characteristics** (T<sub>c</sub>=25°C Unless Otherwise Noted)

•	Deverator	Test Candition	Х				
100V/150 A	Parameter	Test Condition	Min.	Тур.	Max.	Unit	
Static Cha	racteristics						
$BV_{DSS}$	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	100			V	
I	Zero Coto Voltago Droin Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	T <sub>J</sub> =125°C			30	μA	
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA	2		4	V	
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±25V, V <sub>DS</sub> =0V			±100	nA	
R <sub>DS(ON)</sub>	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =75A		3.2	4	mΩ	
. ,	racteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	I <sub>SD</sub> =75A, V <sub>GS</sub> =0V			1.2	V	
trr	Reverse Recovery Time			36		ns	
Qrr	Reverse Recovery Charge	Is⊳=75A, dIs⊳/dt=100A/µs		28		nC	
Dynamic C	haracteristics <sup>©</sup>	•	-	-			
$R_{G}$	Gate Resistance	V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,F=1MHz		2.1		Ω	
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V,		3650		pF ns	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =50V, Frequency=1.0MHz		750			
C <sub>rss</sub>	Reverse Transfer Capacitance			27			
t <sub>d(ON)</sub>	Turn-on Delay Time			24			
t <sub>r</sub>	Turn-on Rise Time	V <sub>DD</sub> =50V,I <sub>DS</sub> =75A,		13			
$t_{d(OFF)}$	Turn-off Delay Time	$V_{GEN}$ =10V, $R_{G}$ =4.7 $\Omega$		49			
t <sub>f</sub>	Turn-off Fall Time			17			
Gate Char	ge Characteristics						
Qg	Total Gate Charge			87			
$Q_gs$	Gate-Source Charge	V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>DS</sub> =75A		23		nC	
$Q_gd$	Gate-Drain Charge			15			

Notes: ①Pulse width limited by safe operating area.

②Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.

3Limited by  $T_{Jmax}\text{, }I_{AS}$  =42A,  $V_{DD}$  = 60V,  $R_{G}$  = 50 $\Omega$  , Starting  $T_{J}$  = 25°C.

④ Pulse test; Pulse width  $\leq$  300µs, duty cycle  $\leq$  2%.

5 Guaranteed by design, not subject to production testing.



100V N-Channel Enhancement Mode Power MOSFET

## **Typical Characteristics**







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XPX150N10TU

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# **Avalanche Test Circuit and Waveforms**



Switching Time Test Circuit and Waveforms



## **Ordering and Marking Information**

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
XPX150N10TU	XPX150N10TU	TO220	Tube	50	-	-



Package Information

TO220





100V N-Channel Enhancement Mode Power MOSFET

SYMBOL		MM			INCH		SYMBOL		MM			INCH	
DIMDOL	MIN	NOM	MAX	MIN	NOM	MAX	SIMDOL	MIN	NOM	MAX	MIN	NOM	MAX
А	4.30	4.50	4.70	0.169	0.177	0.185	Φpl	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.15	1.30	1.40	0.045	0.051	0.055	е		2.54 BSC			0.10 BSC	
A2	1.90	2.25	2.60	0.075	0.089	0.102	e1		5.08 BSC			0.20 BSC	
b	0.60	0.80	1.00	0.024	0.031	0.039	H1	6.35	6.50	6.80	0.250	0.256	0.268
b2	1.17	1.28	1.72	0.046	0.050	0.068	L	12.70	13.18	13.65	0.500	0.519	0.537
С	0.40	0.50	0.60	0.016	0.020	0.024	L1	*	*	3.95	*	*	0.156
D	15.40	15.70	16.00	0.606	0.618	0.630	L2		2.50 REF			0.098 REF	7
D1	8.96	9.21	9.46	0.353	0.363	0.372	Фр	3.50	3.60	3.75	0.138	0.142	0.148
DEP	*	*	0.30	*	*	0.012	Q	2.70	2.80	3.20	0.106	0.110	0.126
E	9.66	9.97	10.28	0.380	0.393	0.405	θ1	5°	7°	9°	5°	7°	9°
E1	*	8.70	*	*	0.343	*	θ2	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.402							



#### 100V N-Channel Enhancement Mode Power MOSFET

#### Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time		
Pb device	245℃ <b>±5</b> ℃	5sec±1sec		
Pb-Free device	<b>260</b> ℃ <b>+0/-5</b> ℃	5sec±1sec		



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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